2SB0956

Silicon PNP epitaxial planar type

For low-frequency output amplification Complementary to 2SD1280

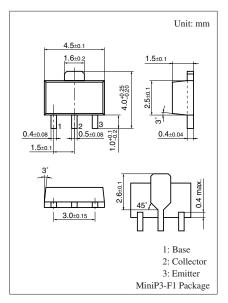
■ Features

- Large collector power dissipation P_C
- Low collector-emitter saturation voltage V_{CE(sat)}
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-20	V	
Collector-emitter voltage (Base open)	V _{CEO}	-20	V	
Emitter-base voltage (Collector open)	V_{EBO}	-5	V	
Collector current	I_C	-1	A	
Peak collector current	I_{CP}	-2	A	
Collector power dissipation *	P_{C}	1	W	
Junction temperature	T_{j}	150	°C	
Storage temperature	T_{stg}	-55 to +150	°C	

Note) *: Print circuit board: Copper foil area of 1 $\rm cm^2$ or more, and the board thickness of 1.7 mm for the collector portion



Marking Symbol: H

■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -1 \text{ mA}, I_{\rm B} = 0$	-20			V
Emiter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \ \mu A, \ I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -10 \text{ V}, I_E = 0$			-1	μΑ
Forward current transfer ratio *1	h _{FE1} *2	$V_{CE} = -2 \text{ V}, I_{C} = -500 \text{ mA}$	130		280	_
	h _{FE2}	$V_{CE} = -2 \text{ V}, I_{C} = -1.5 \text{ A}$	50			
Collector-emitter saturation voltage *1	V _{CE(sat)}	$I_C = -1 \text{ A}, I_B = -50 \text{ mA}$			- 0.5	V
Base-emitter saturation voltage *1	V _{BE(sat)}	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$			-1.2	V
Transition frequency	f_T	$V_{CB} = -6 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -6 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		40		pF
(Common base, input open circuited)						

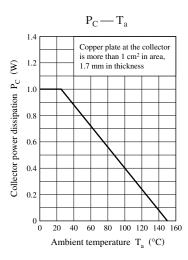
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

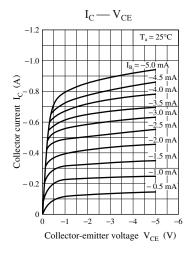
2. *1: Pulse measurement

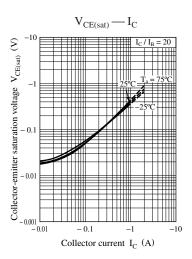
*2: Rank classification

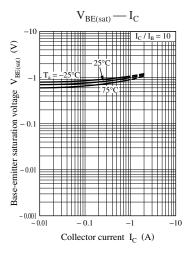
Rank	R	S
h_{FE1}	130 to 210	180 to 280

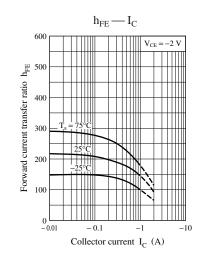
Panasonic

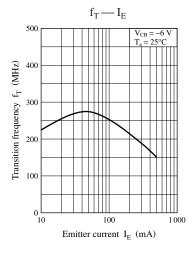


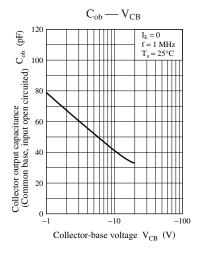


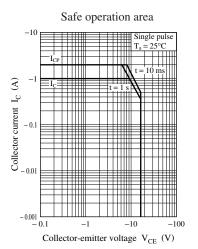












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